

Title (en)

Resin-moulded semiconductor hybrid module and manufacturing method thereof

Title (de)

Hybrid-Halbleitermodul aus vergossenem Kunstharz und Verfahren zuseiner Herstellung

Title (fr)

Module sémiconducteur de type hybride moulé en résine et procédé de sa fabrication

Publication

EP 0936671 A1 19990818 (EN)

Application

EP 99101733 A 19990211

Priority

JP 2949198 A 19980212

Abstract (en)

A semiconductor device includes a main circuit part having a semiconductor device formed on an electrode plate (13) of a lead frame and a control circuit part having protective functions, which is integrally molded by a resin mold part (30) into an integral mold structure. <IMAGE>

IPC 1-7

H01L 25/16; **H01L 23/433**

IPC 8 full level

H01L 25/07 (2006.01); **H01L 23/433** (2006.01); **H01L 25/16** (2006.01); **H01L 25/18** (2006.01)

CPC (source: EP KR US)

H01L 23/4334 (2013.01 - EP US); **H01L 23/52** (2013.01 - KR); **H01L 25/165** (2013.01 - EP US); **H01L 24/45** (2013.01 - EP US); **H01L 24/48** (2013.01 - EP US); **H01L 2224/45015** (2013.01 - EP US); **H01L 2224/45124** (2013.01 - EP US); **H01L 2224/45144** (2013.01 - EP US); **H01L 2224/48091** (2013.01 - EP US); **H01L 2224/48137** (2013.01 - EP US); **H01L 2224/48247** (2013.01 - EP US); **H01L 2224/48257** (2013.01 - EP US); **H01L 2224/73265** (2013.01 - EP US); **H01L 2924/01079** (2013.01 - EP US); **H01L 2924/1305** (2013.01 - EP US); **H01L 2924/13055** (2013.01 - EP US); **H01L 2924/13091** (2013.01 - EP US); **H01L 2924/14** (2013.01 - EP US); **H01L 2924/181** (2013.01 - EP US); **H01L 2924/19041** (2013.01 - EP US); **H01L 2924/19107** (2013.01 - EP US)

Citation (search report)

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